	Type	Hits	Search Text	DBs	Time Stamp	Comments	ErrorDefinitio	Errors
1	BRS	32	nano$ with wide with bandgap and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:08			0
2	BRS	35	nano$ with wide with bandgap	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:43			0
3	BRS	22	nano$ with wide with bandgap and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:44			0
4	BRS	22	nano$ with wide with bandgap and beam and energy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:46			0
5	BRS	2	nano$ with wide with bandgap and beam and second near energy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:44			0
6	BRS	17	nano$ with wide with bandgap and beam and energy and heat$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:54			0
7	BRS	4	nano$ with wide with bandgap and beam and energy and heat$4 with (source or drain or gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/11 23:58			0
8	BRS	3	nano$ with wide with bandgap and beam and energy and heat$4 and source and drain and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:03			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	ErrorDefinitio	Errors
9	BRS	3	nano$ with wide with bandgap and heat$4 and source and drain and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:06			0
10	BRS	1	nano$ with wide with bandgap and heat$4 with dop$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:05			0
11	BRS	4	nano$ with wide with bandgap and source and drain and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:12			0
12	BRS	11	4697197.URPN.	USPAT	2004/08/12 00:08			0
13	BRS	53	nano$ and wide with bandgap and source and drain and gate and heat$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:13			0
14	BRS	51	nano$ and wide with bandgap and source and drain and gate and heat$5 and dop$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:13			0
15	BRS	49	nano$ and wide with bandgap and source and drain and gate and heat$5 and dop$5 and semiconduct$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:19			0
16	BRS	19	nano$ and wide with bandgap and source and (drain or gate) with heat$5 and dop$5 and semiconduct$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:21			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Record Definitio	Errors
17	BRS	2	nano$ and wide with bandgap and source and (drain or gate) with heat$5 and dop$5 and semiconduct$5 and (single near crystal or monocrystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:30			0
18	BRS	18	nano$ and wide with bandgap and source and drain and gate and heat$5 and dop$5 and semiconduct$5 and (single near crystal or monocrystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:32			0
19	BRS	15	nano$ and wide with bandgap and source and drain and gate and heat$5 and dop$5 and semiconduct$5 and (single near crystal or monocrystal) and laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:33			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error Definitio	Errors
20	BRS	10	nano$ and wide with bandgap and source and drain and gate and heat$5 and dop$5 and semiconduct$5 and (single near crystal or monocrystal) and (laser near beam or electron near beam or charg$4 near particl$4 or ion near beam or electromagnet$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 00:36			0
21	BRS	29	nano$ with wide adj bandgap and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 18:25			0
22	BRS	3	nano$ with wide adj bandgap and semiconductor and (heat$5 or thermal) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 18:27			0
23	BRS	24	nano$ with wide adj bandgap and semiconductor and (heat$5 or thermal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/12 18:28			0
24	BRS	0	wide with bandgap with irradiat$6 with laser and nano$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:10			0

	Typ e	Hi ts	Search Text	DBs	Time Stamp	Comments	ErrorDefinitio	Errors
25	BRS	0	wide with bandgap with iradiat$6 with laser and nano$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:10			0
26	BRS	19	wide with (bandgap or band with gap) with laser and nano$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:20			0
27	BRS	4	wide with (bandgap or band with gap) and laser with nano$8 with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:27			0
28	BRS	28	wide with (bandgap or band with gap) and laser and nano$8 with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:27			0
29	BRS	1	wide with (bandgap or band with gap) with laser and nano$8 with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:28			0
30	BRS	0	wide with (bandgap or band with gap) and irradiat$ with laser and nano$8 with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:29			0
31	BRS	16 8	wide with (bandgap or band with gap) and irradiat$ with laser	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:29			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	ErrorDefinitio	Errors
32	BRS	50	wide with (bandgap or band with gap) and irradiat$ with laser and nano$8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:30			0
33	BRS	20	wide with (bandgap or band with gap) and irradiat$ with laser and nano$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:38			0
34	BRS	31	wide with (bandgap or band with gap) and laser with nano$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:46			0
35	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat$6 or eb or electron near beam or thermal$4) with nano$8 and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:48			0
36	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat$6 or eb or electron near beam or thermal$4) and nano$ and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:49			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	ErrorDefinitio	Errors
37	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat$6 or eb or electron near beam or thermal$4) and nano$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:49			0
38	BRS	167	wide with (bandgap or band with gap) with (laser or beam or heat$6 or eb or electron near beam or thermal$4) and nano$	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:49			0
39	BRS	2	wide with (bandgap or band with gap) with (laser or beam or heat$6 or eb or electron near beam or thermal$4) and nano$ with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 22:50			0
40	BRS	54	wide with (bandgap or band with gap) and (laser or beam or heat$6 or eb or electron near beam or thermal$4) and nano$ with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:29			0

	Typ e	Hi ts	Search Text	DBs	Time Stamp	Comments	ErrorDefinitio	Errors
41	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat$6 or eb or electron near beam or thermal$4) and nano$ with transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:29			0
42	BRS	0	wide with (bandgap or band with gap) near (laser or beam or heat$6 or eb or electron near beam or thermal$4) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:30			0
43	BRS	25 8	wide with (bandgap or band with gap) with (laser or beam or heat$6 or eb or electron near beam or thermal$4) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:30			0
44	BRS	17	wide with (bandgap or band with gap) with second with (laser or beam or heat$6 or eb or electron near beam or thermal$4) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/19 23:31			0